

SIGC109T120R3

IGBT³ Chip

FEATURES:

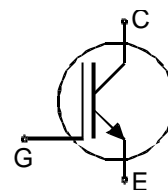
- 1200V Trench + Field Stop technology
- low turn-off losses
- short tail current
- positive temperature coefficient
- easy paralleling

This chip is used for:

- power module

Applications:

- drives



Chip Type	V _{CE}	I _{CN}	Die Size	Package	Ordering Code
SIGC109T120R3	1200V	100A	10.47 x 10.44 mm ²	sawn on foil	Q67050-A4108-A001

MECHANICAL PARAMETER:

Raster size	10.47 x 10.44	mm
Emitter pad size	8x(2.11x4.41)	
Gate pad size	1.14 x 1.14	
Area total / active	109.3 / 85.8	mm ²
Thickness	140	μm
Wafer size	150	mm
Flat position	90	grd
Max.possible chips per wafer	124	
Passivation frontside	Photoimide	
Emitter metallization	3200 nm Al Si 1%	
Collector metallization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, <500μm	
Reject Ink Dot Size	tbd	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month	

MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	1200	V
DC collector current, limited by T_{jmax}	I_C	100	A
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	200	A
Gate emitter voltage	V_{GE}	± 20	V
Operating junction and storage temperature	T_j, T_{stg}	-55 ... +150	$^{\circ}\text{C}$

STATIC CHARACTERISTICS (tested on chip), $T_j=25^{\circ}\text{C}$, unless otherwise specified:

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0\text{V}, I_C=4\text{mA}$	1200			V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE}=15\text{V}, I_C=100\text{A}$	1.3	1.7	2.1	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=4\text{mA}, V_{GE}=V_{CE}$	5.0	5.8	6.5	
Zero gate voltage collector current	I_{CES}	$V_{CE}=1200\text{V}, V_{GE}=0\text{V}$			650	μA
Gate-emitter leakage current	I_{GES}	$V_{CE}=0\text{V}, V_{GE}=30\text{V}$			600	nA
Integrated gate resistor	R_{Gint}			7.5		Ω

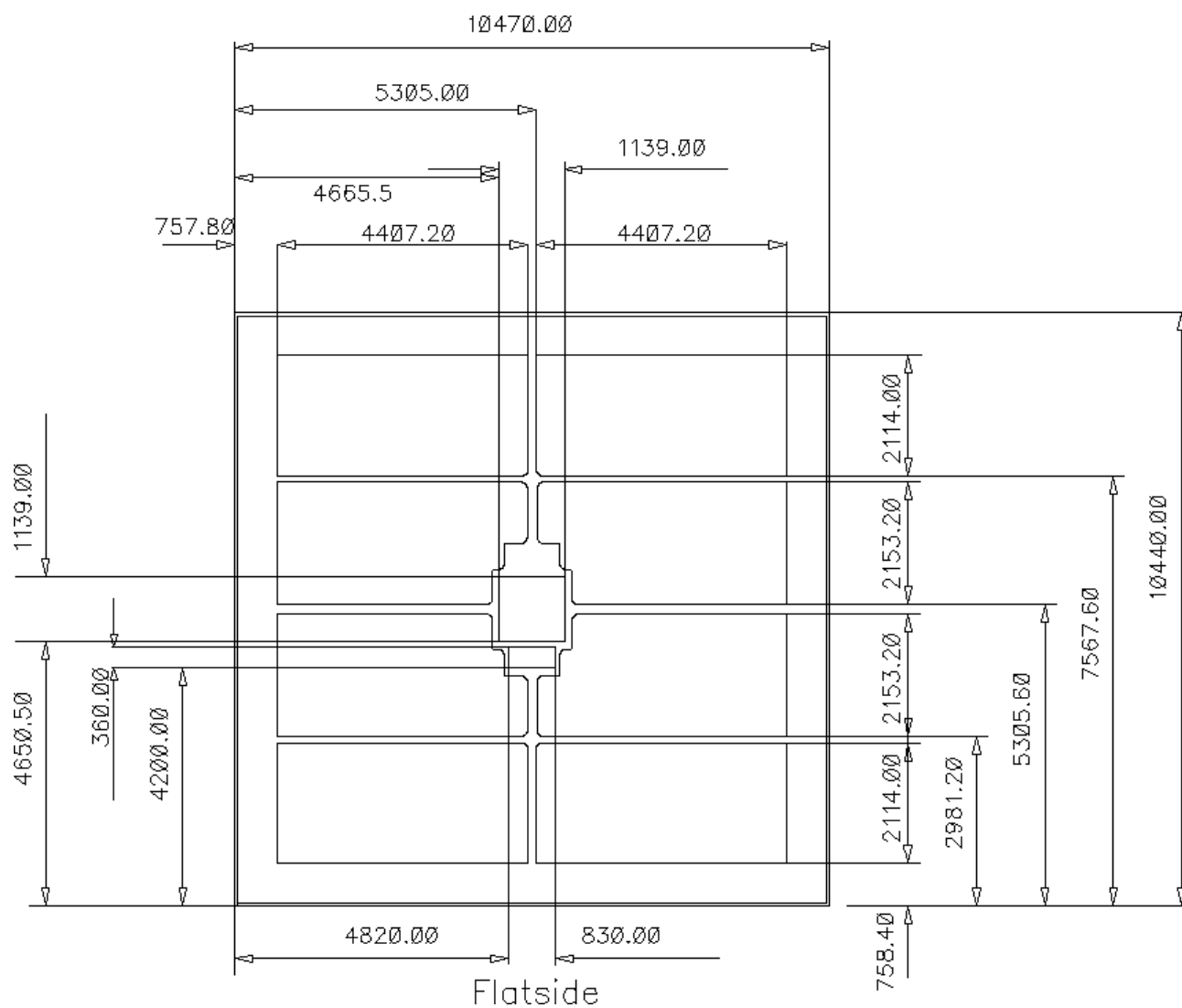
ELECTRICAL CHARACTERISTICS (tested at component):

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	C_{iss}	$V_{CE}=25\text{V},$ $V_{GE}=0\text{V},$ $f=1\text{MHz}$		tbd		nF
Output capacitance	C_{oss}			tbd		
Reverse transfer capacitance	C_{rss}			tbd		

SWITCHING CHARACTERISTICS (tested at component), Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Turn-on delay time	$t_{d(on)}$	$T_j=125^{\circ}\text{C}$ $V_{CC}=600\text{V},$ $I_C=100\text{A},$ $V_{GE}=-15/15\text{V},$ $R_G=--\Omega$		tbd		μs
Rise time	t_r			tbd		
Turn-off delay time	$t_{d(off)}$			tbd		
Fall time	t_f			tbd		

CHIP DRAWING:





Preliminary

SIGC109T120R3

FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet	tbd	
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DESCRIPTION:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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